

### **100V N-Channel Enhancement Mode MOSFET**

Current

18A

### Features

Voltage

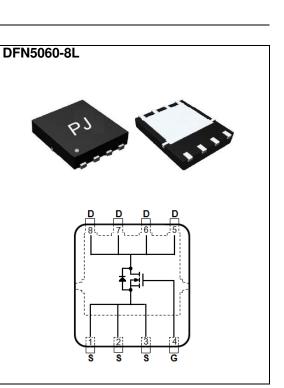
• RDS(ON), VGS@10V, ID@18A<50m $\Omega$ 

100 V

- RDS(ON) , VGS@4.5V, ID@15A<55mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### **Mechanical Data**

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0028 ounces, 0.08 grams
- Marking: Q5474A



## **Maximum Ratings and Thermal Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	100	V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20	V
Continuous Drain Current		I <sub>D</sub>	18	А
Pulsed Drain Current		I <sub>DM</sub>	36	A
Single Pulse Avalanche Energy (Note 5)		E <sub>AS</sub>	16.2	mJ
Power Dissipation	T <sub>C</sub> =25°C	P <sub>D</sub>	52	W
	Derate above 25°C		416	mW/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal resistance				
- Junction to Ambient, t<10s (Note 3)		$R_{ extsf{ heta}JC}$	2.4	°C/W

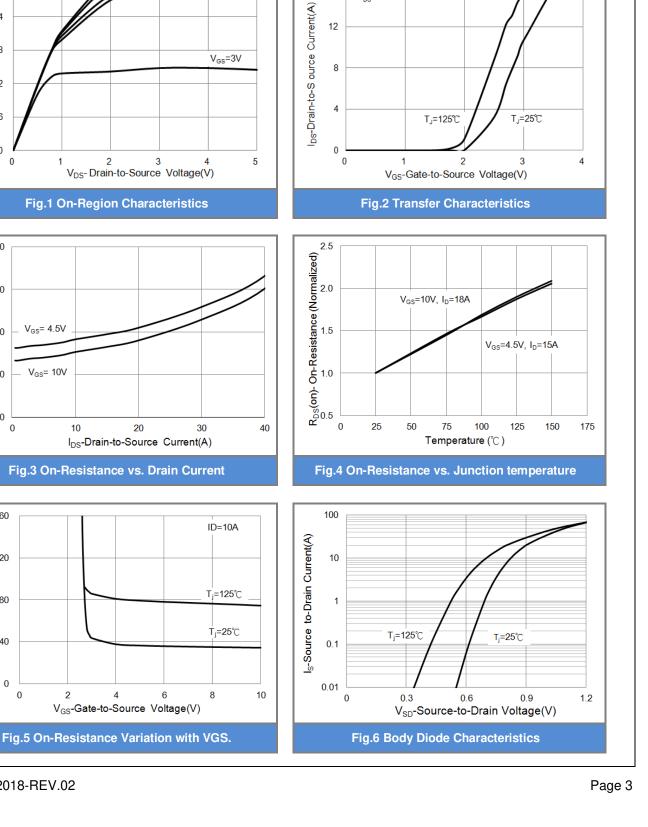


## **Electrical Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V,I_{D}=250uA$	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250$ uA	1.0	1.5	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}$ =10V, $I_{D}$ =18A	-	37	50	mΩ
		$V_{GS}$ =4.5V,I <sub>D</sub> =15A	-	38	55	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =80V,V <sub>GS</sub> =0V	-	0.03	1.0	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	<u>+</u> 10	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	$Q_{g}$	V <sub>DS</sub> =80V, I <sub>D</sub> =18A, V <sub>GS</sub> =10V <sup>(Note 1,2)</sup>	-	61	-	nC
Gate-Source Charge	$Q_gs$		-	8.8	-	
Gate-Drain Charge	$Q_gd$		-	11	-	
Input Capacitance	Ciss	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	3555	-	pF
Output Capacitance	Coss		-	119	-	
Reverse Transfer Capacitance	Crss		-	56	-	
Turn-On Delay Time	$td_{(on)}$	$V_{DD}$ =50V, I <sub>D</sub> =18A, $V_{GS}$ =10V, $R_{G}$ =3.3 $\Omega$ <sup>(Note 1,2)</sup>	-	16	-	
Turn-On Rise Time	tr		-	50	-	
Turn-Off Delay Time	$td_{(off)}$		-	64	-	
Turn-Off Fall Time	tf		-	18	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	18	A
Diode Forward Current	۱ <sub>S</sub>					
Diode Forward Voltage	$V_{\text{SD}}$	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V	-	0.7	1.2	v

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 5. The test condition is L=0.1mH,  $I_{AS}{=}18A,\,V_{DD}{=}25V,\,V_{GS}{=}10V$
- 6. R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 7. Guaranteed by design, not subject to production testing.



16

12

8

4

V<sub>GS</sub>=3V

V<sub>DS</sub>=5V

# **PJQ5474A**

10V,8V,5V, 4.5V

**TYPICAL CHARACTERISTIC CURVES** 

30

0

60

50

40

30

20

160

120

80

40

0

0

 $R_{DS}(on)$ - On-Resistance(m $\Omega$ )

0

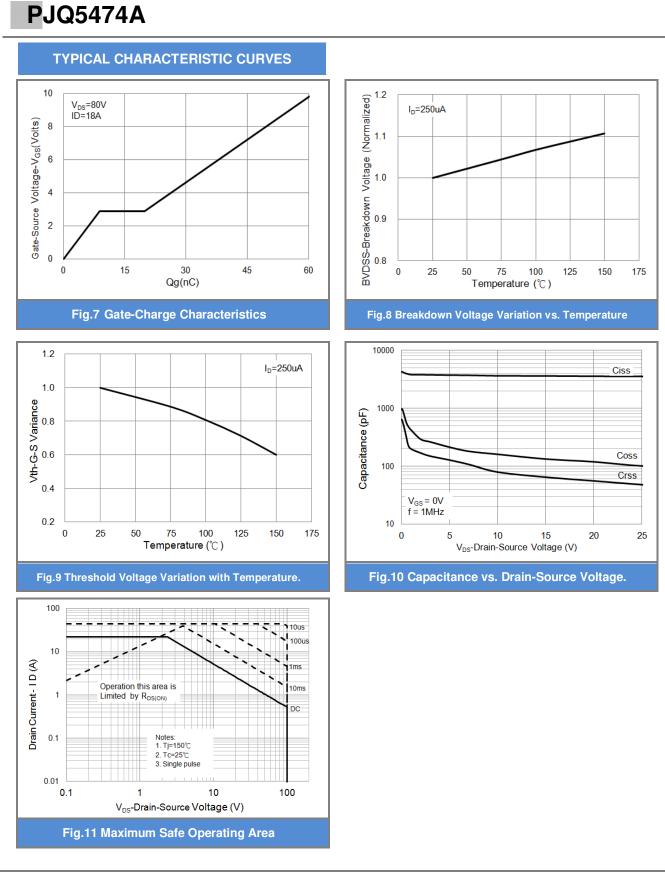
 $R_{DS}(on)$ - On-Resistance(m $\Omega$ )

0



T\_**=25°**℃

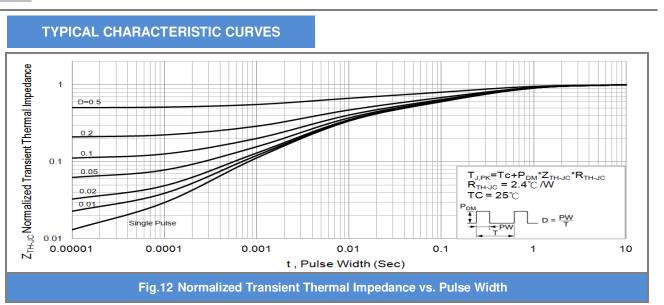
T<sub>J</sub>=125℃





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# **PJQ5474A**



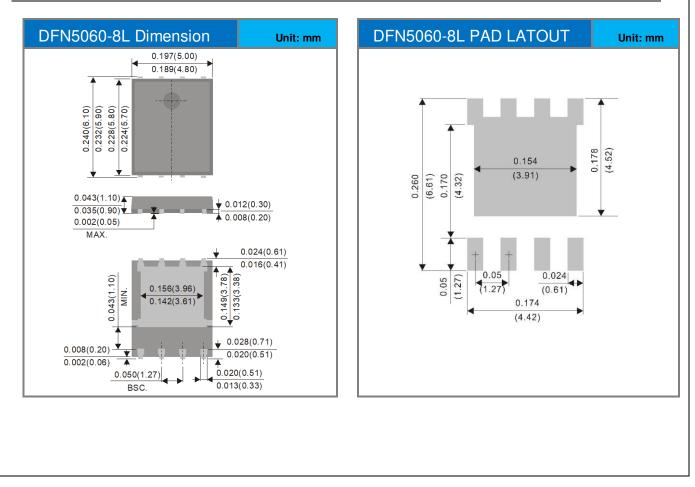




## PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJQ5474A_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5474A	Halogen free

## Packaging Information & Mounting Pad Layout





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